

## Description

The PSM8N10R4 uses split gate trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for power management and high efficiency applications at high switching frequencies applications.

### MOSFET Product Summary

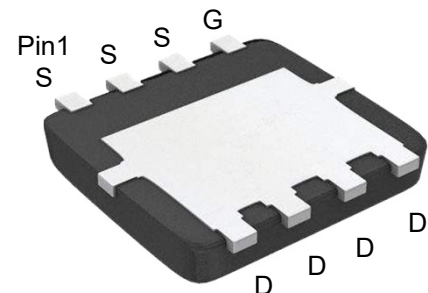
| $V_{DS}(V)$ | $R_{DS(on)}(m\Omega)(Typ)$ | $I_D(A)$ |
|-------------|----------------------------|----------|
| 100         | 3.2@ $V_{GS} = 10V$        | 135      |

## Feature

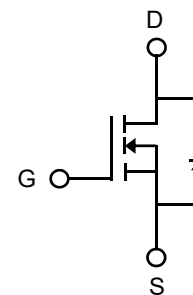
- Low  $R_{DS(ON)}$  - Ensures On-State Losses are Minimized
- Excellent  $Q_{gd} \times R_{DS(ON)}$  Product(FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package  
Enables Higher Density End Products
- 100% UIS (Avalanche) Rated
- Lead-Free Finish ; RoHS Compliant
- Halogen and Antimony Free. "Green" Device

## Applications

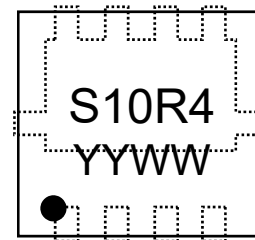
- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers



**PDFN5060-8L  
(Bottom View)**



**Circuit Diagram**



**Pin1  
Marking (Top View)**

## Absolute maximum rating@25°C

| Rating                                               |                   | Symbol          | Value    | Units        |
|------------------------------------------------------|-------------------|-----------------|----------|--------------|
| Drain-Source Voltage                                 |                   | $V_{DS}$        | 100      | V            |
| Gate-Source Voltage                                  |                   | $V_{GS}$        | $\pm 20$ | V            |
| Drain Current-Continuous <sup>1)</sup>               | $T_C=25^\circ C$  | $I_D$           | 135      | A            |
|                                                      | $T_C=100^\circ C$ |                 | 85       |              |
| Pulsed Drain Current <sup>2)</sup>                   |                   | $I_{DM}$        | 539      | A            |
| Total Power Dissipation <sup>4)</sup>                | $T_C=25^\circ C$  | $P_D$           | 125      | W            |
|                                                      | $T_C=100^\circ C$ |                 | 50       |              |
| Avalanche Current @ $L=0.1mH$                        |                   | $I_{AS}$        | 72       | A            |
| Avalanche Energy @ $L=0.1mH$                         |                   | $E_{AS}$        | 259      | mJ           |
| Thermal Resistance , Junction-to-Case <sup>4)</sup>  |                   | $R_{\theta JC}$ | 1.0      | $^\circ C/W$ |
| Thermal Resistance Junction-to-Ambient <sup>3)</sup> |                   | $R_{\theta JA}$ | 43       | $^\circ C/W$ |
| Junction and Storage Temperature Range               |                   | $T_J, T_{STG}$  | -55~+150 | $^\circ C$   |

## Electrical characteristics per line@25°C (unless otherwise specified)

| Parameter                                        | Symbol              | Conditions                                                                                   | Min.                 | Typ. | Max. | Units |    |
|--------------------------------------------------|---------------------|----------------------------------------------------------------------------------------------|----------------------|------|------|-------|----|
| Off Characteristics                              |                     |                                                                                              |                      |      |      |       |    |
| Drain-Source Breakdown Voltage                   | BV <sub>DSS</sub>   | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA                                                 | 100                  | -    | -    | V     |    |
| Zero Gate Voltage Drain Current                  | I <sub>DSS</sub>    | V <sub>DS</sub> = 100V,<br>V <sub>GS</sub> = 0V                                              | T <sub>J</sub> =25°C | -    | -    | 1.0   | μA |
|                                                  |                     |                                                                                              | T <sub>J</sub> =55°C | -    | -    | 10    |    |
| Gate-Body Leakage Current                        | I <sub>GSS</sub>    | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V                                                 | -                    | -    | ±100 | nA    |    |
| On Characteristics <sup>5)</sup>                 |                     |                                                                                              |                      |      |      |       |    |
| Gate Threshold Voltage                           | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                                   | 2.0                  | 3.0  | 4.0  | V     |    |
| Drain-Source On-State Resistance                 | R <sub>DS(ON)</sub> | V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A                                                  | -                    | 3.2  | 3.8  | mΩ    |    |
| Forward Transconductance                         | g <sub>fs</sub>     | V <sub>DS</sub> = 5 V, I <sub>D</sub> = 20A                                                  | -                    | 46   | -    | S     |    |
| Diode Forward Voltage                            | V <sub>SD</sub>     | V <sub>GS</sub> = 0V, I <sub>S</sub> = 2A                                                    | -                    | 0.7  | 1.2  | V     |    |
| Dynamic Characteristics <sup>6)</sup>            |                     |                                                                                              |                      |      |      |       |    |
| Input Capacitance                                | C <sub>iss</sub>    | V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz                                   | -                    | 4799 | -    | pF    |    |
| Output Capacitance                               | C <sub>oss</sub>    |                                                                                              | -                    | 1256 | -    |       |    |
| Reverse Transfer Capacitance                     | C <sub>rss</sub>    |                                                                                              | -                    | 50   | -    |       |    |
| Switching Characteristics <sup>6)</sup>          |                     |                                                                                              |                      |      |      |       |    |
| Turn-on Delay Time                               | t <sub>d(on)</sub>  | V <sub>DS</sub> = 50V, V <sub>GS</sub> = 10V,<br>R <sub>GEN</sub> = 3Ω, I <sub>D</sub> = 20A | -                    | 10   | -    | ns    |    |
| Turn-on Rise Time                                | t <sub>r</sub>      |                                                                                              | -                    | 17   | -    |       |    |
| Turn-Off Delay Time                              | t <sub>d(off)</sub> |                                                                                              | -                    | 44   | -    |       |    |
| Turn-Off Fall Time                               | t <sub>f</sub>      |                                                                                              | -                    | 23   | -    |       |    |
| Total Gate Charge                                | Q <sub>g</sub>      | V <sub>DS</sub> = 50V, I <sub>D</sub> = 20A,<br>V <sub>GS</sub> = 0 to 10V                   | -                    | 68   | -    | nC    |    |
| Gate-Source Charge                               | Q <sub>gs</sub>     |                                                                                              | -                    | 19   | -    |       |    |
| Gate-Drain Charge                                | Q <sub>gd</sub>     |                                                                                              | -                    | 15   | -    |       |    |
| Gate Resistance                                  | R <sub>g</sub>      | V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz                                             | -                    | 1.7  | -    | Ω     |    |
| Drain-Source Diode Characteristics <sup>6)</sup> |                     |                                                                                              |                      |      |      |       |    |
| Reverse Recovery Time                            | t <sub>rr</sub>     | I <sub>F</sub> =20A, d <sub>I</sub> /d <sub>t</sub> =100A/μs                                 | -                    | 62   | -    | ns    |    |
| Reverse Recovery Charge                          | Q <sub>rr</sub>     |                                                                                              | -                    | 130  | -    | nC    |    |
| Diode Forward Current                            | I <sub>S</sub>      | -                                                                                            | -                    | -    | 135  | A     |    |

## Notes:

1. Pulse width limited by maximum junction temperature.
2. Pulse test : Pulse width  $\leq 100\mu s$ , duty cycle  $\leq 2\%$ .
3. Device mounted on 1 inch FR4 PCB with 2oz.Copper.
4. Device mounted on infinite heatsink.
5. Measured under pulsed conditions. Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
6. Guaranteed by design, not subject to production.

## Typical Characteristics

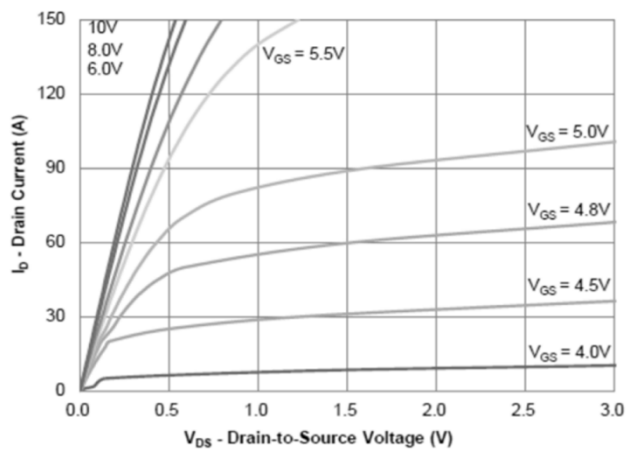


Figure 1: Output Characteristics

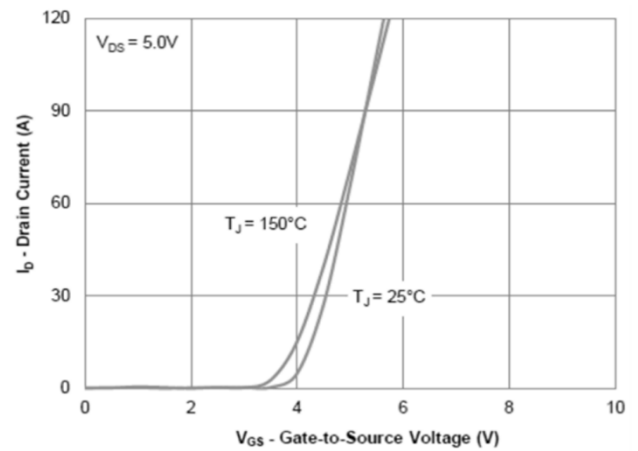


Figure 2: Transfer Characteristics

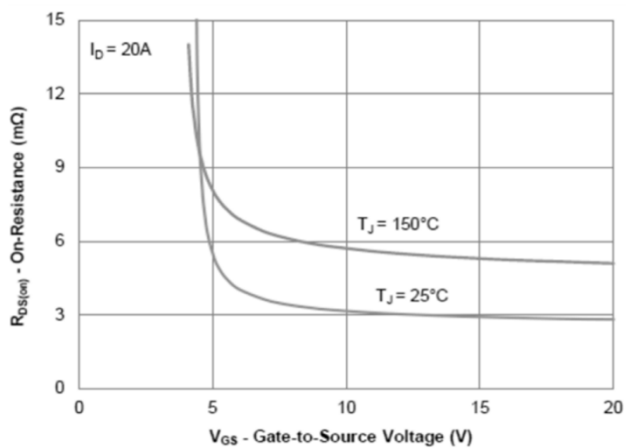


Figure 3: On-Resistance vs. Gate-Source Voltage

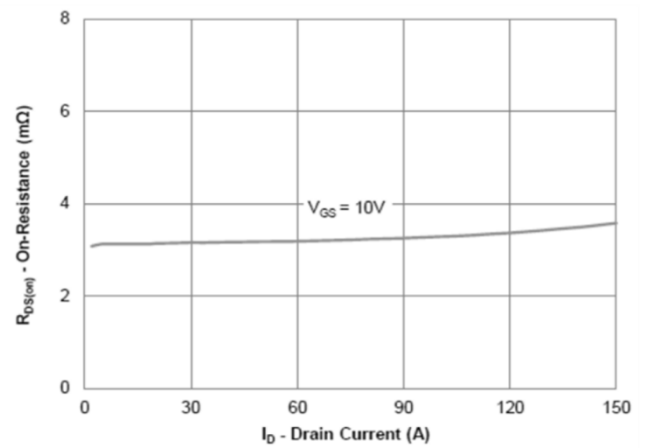


Figure 4: On-Resistance vs. Drain Current

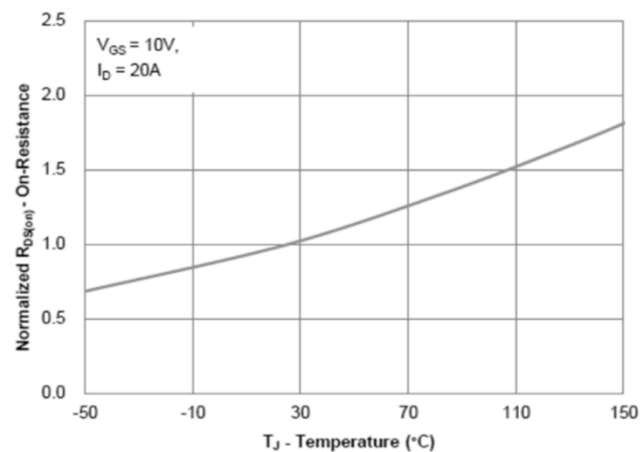


Figure 5: On-Resistance vs. Junction Temperature

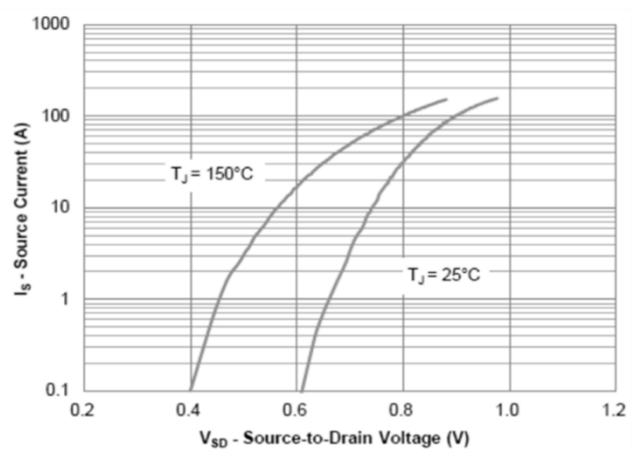


Figure 6: Source-Drain Diode Forward Voltage

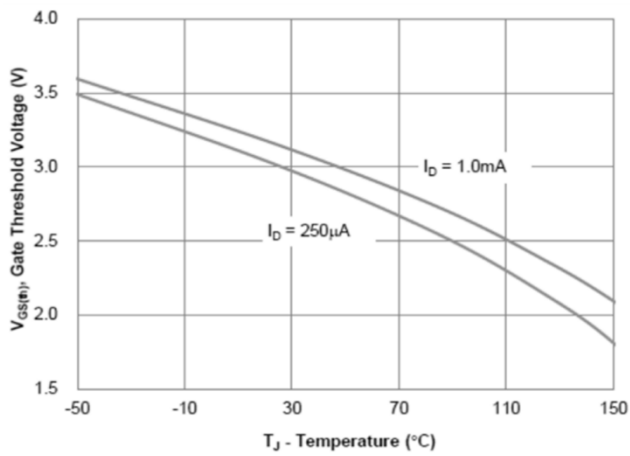


Figure 7: Gate Threshold Variation vs. Junction Temperature

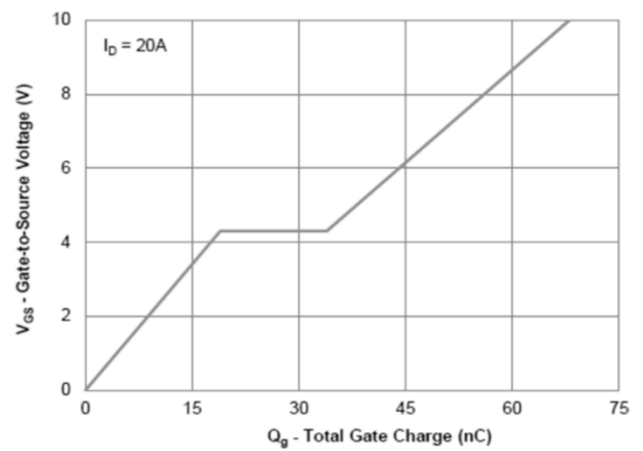


Figure 8: Gate Charge Characteristics

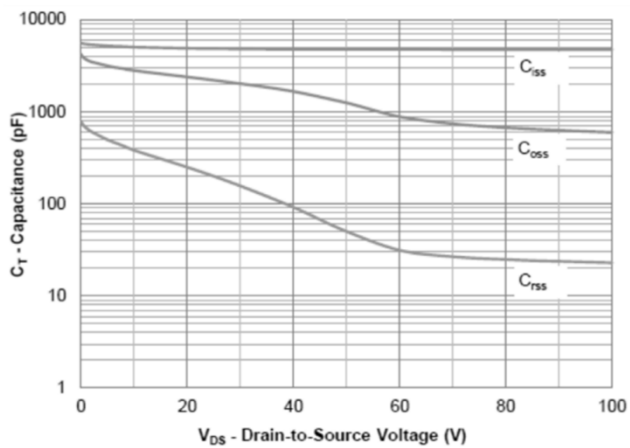


Figure 9: Capacitance Characteristics

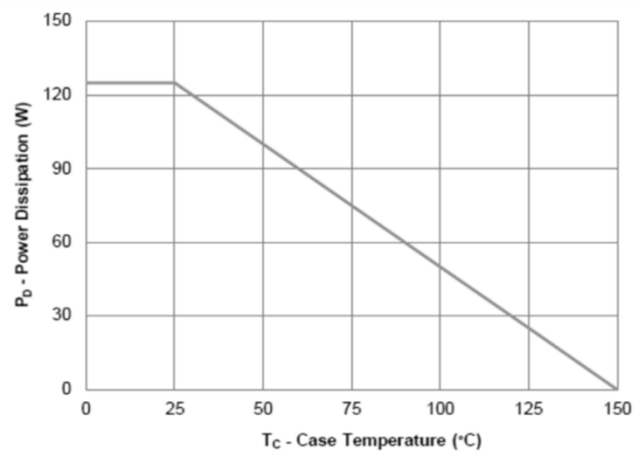


Figure 10: Power Derating

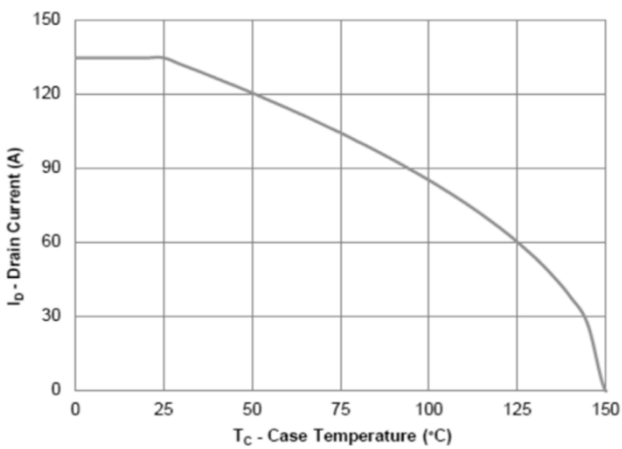


Figure 11: Current Derating

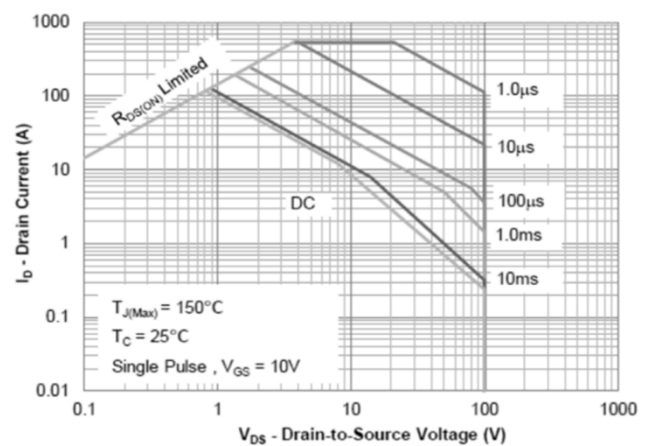


Figure 12: Safe Operating Area

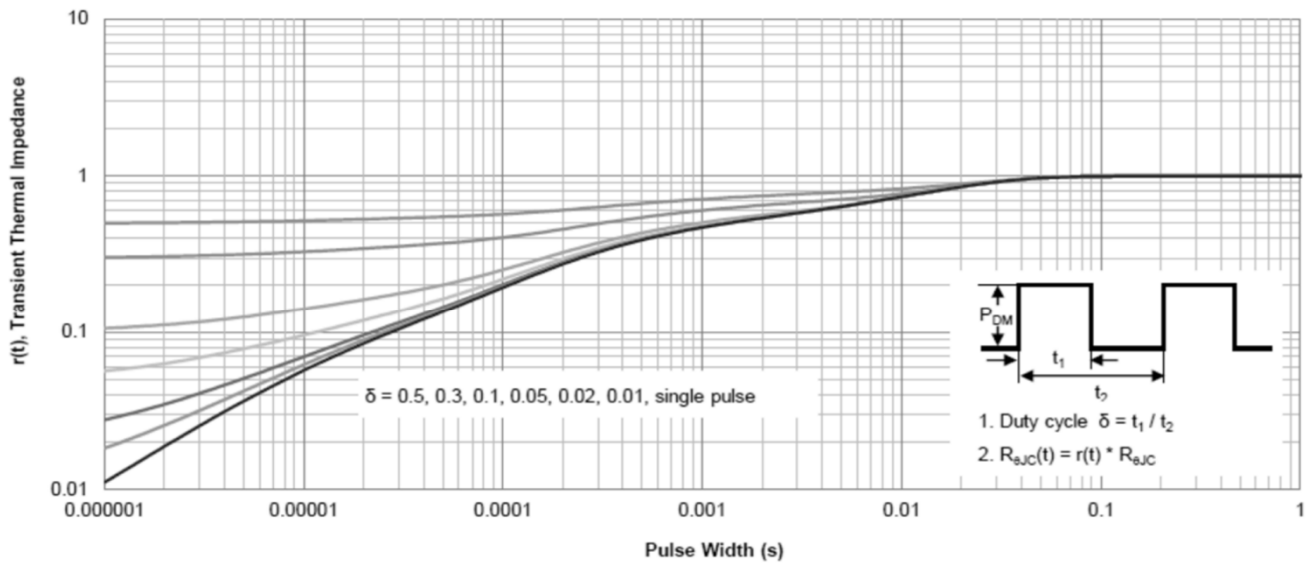
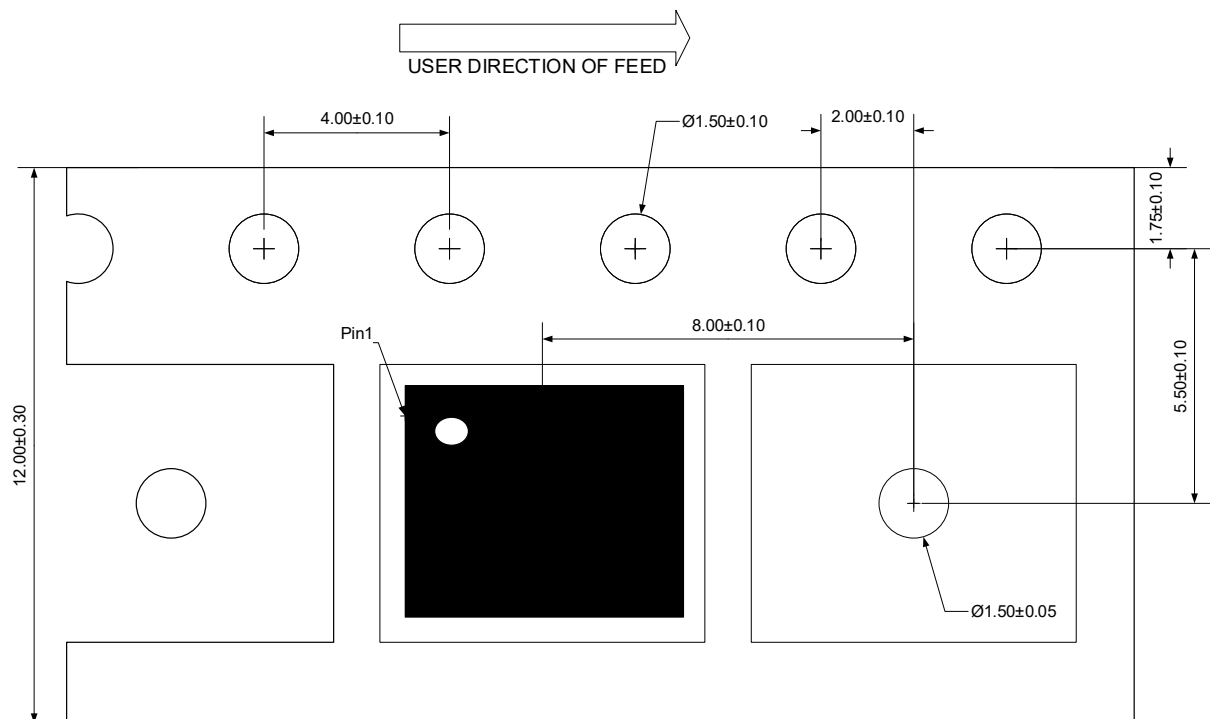


Figure 13: Normalized Maximum Transient Thermal Impedance

## Ordering Information

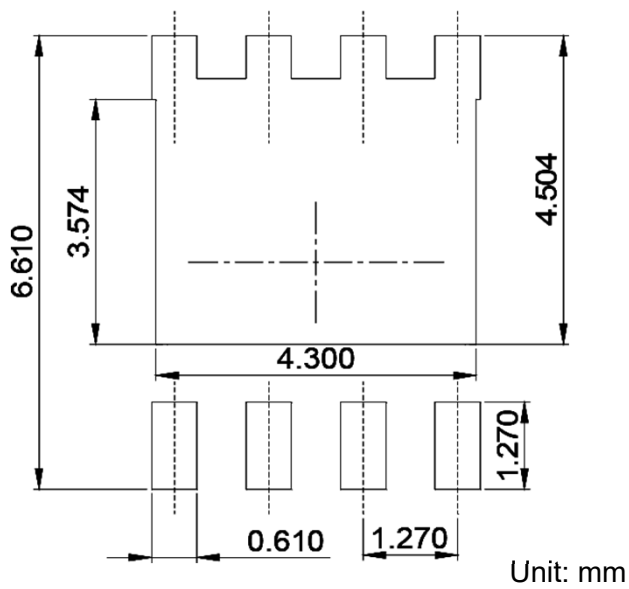
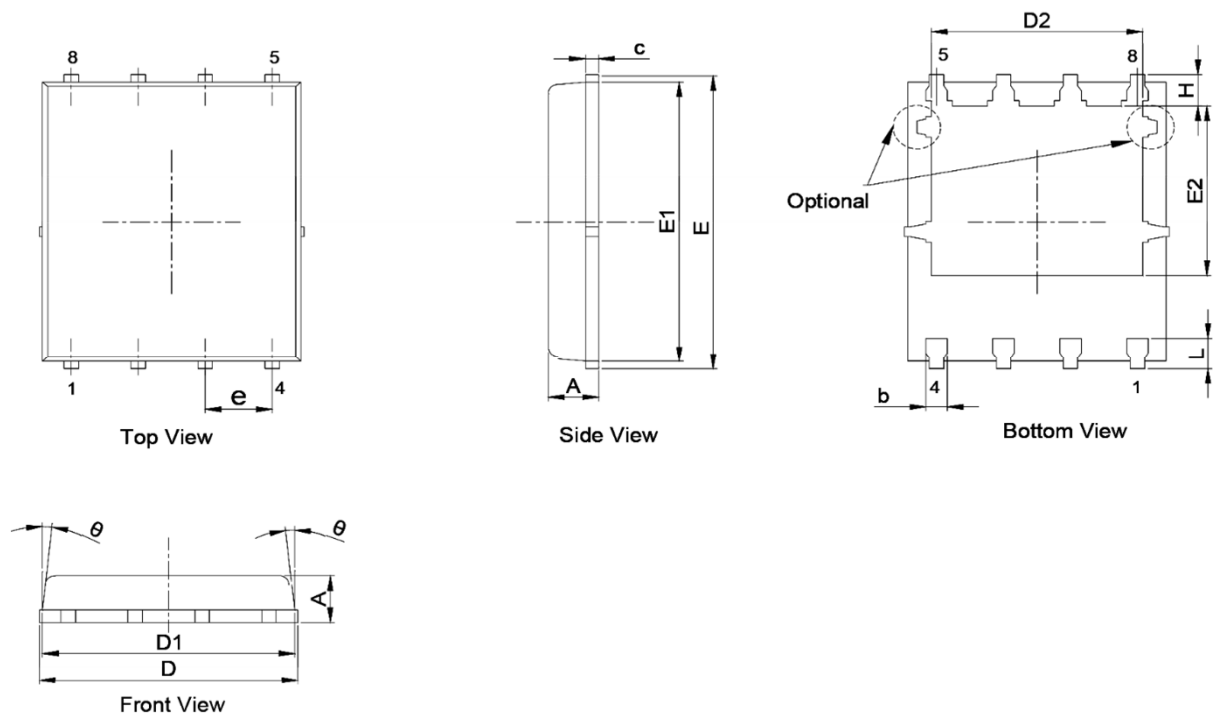
| Device    | Package     | Reel | Shipping           |
|-----------|-------------|------|--------------------|
| PSM8N10R4 | PDFN5060-8L | 13"  | 5000 / Tape & Reel |

## Load With Information



Unit:mm

Product Dimension (PDFN5060-8L)



Suggested PCB Layout

| Dim      | Millimeters |      | Inches     |       |
|----------|-------------|------|------------|-------|
|          | Min         | Max  | Min        | Max   |
| A        | 0.90        | 1.10 | 0.035      | 0.043 |
| b        | 0.20        | 0.51 | 0.008      | 0.020 |
| c        | 0.21        | 0.34 | 0.008      | 0.013 |
| D        | 4.90        | 5.40 | 0.193      | 0.213 |
| D1       | 4.80        | 5.15 | 0.189      | 0.203 |
| D2       | 3.91        | 4.20 | 0.154      | 0.165 |
| E        | 5.90        | 6.50 | 0.232      | 0.256 |
| E1       | 5.65        | 5.95 | 0.222      | 0.234 |
| E2       | 3.32        | 3.63 | 0.131      | 0.143 |
| e        | 1.27 BSC.   |      | 0.050 Ref. |       |
| H        | 0.50        | 0.93 | 0.020      | 0.037 |
| L        | 0.45        | 0.91 | 0.018      | 0.036 |
| $\theta$ | 0°          | 12°  | 0°         | 12°   |

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